Amendments to the Claims:

A clean version of the entire set of pending claims (including amendments to the claims, if any) is submitted herewith per 37 CFR 1.121(c) (3). This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1.-9. (Cancelled)

10. (Currently Amended) A method of depositing a wiring thin film over a semiconductor substrate, the method comprising:

providing a Al_3Ti target;

providing a substrate;

forming a Ti layer over said substrate;

sputter depositing an Al_3Ti layer on said Ti layer using said Al_3Ti target;

and, after the sputter depositing, annealing said substrate at a temperature of at least 400°C to promote absorption of Si into said Al_3Ti layer.

11. (Previously Presented) A method as recited in claim 10, wherein an Al layer is deposited on said Al_3Ti layer.

12. (Previously Presented) A method as recited in claim 10, further comprising pattern-etching said Al layer thereby forming a wiring pattern.

13. (Previously Presented) A method as recited in claim 10, wherein the method further comprises forming an insulating layer between said substrate and said Al_3Ti layer.

14. (Previously Presented) A method of forming a wiring film, the method comprising:

providing a substrate;

depositing a Ti layer over said substrate;

depositing an Al-Si-Cu layer on said Ti layer, which forms an Al_3Ti on said Ti layer;

pattern etching an Al layer, which forms beneath said Al-Si-Cu layer; and

after the depositing of the Al-Si-Cu layer, annealing the substrate at a temperature of at least 400°C.

15. (Previously Presented) A method as recited in claim 14, wherein said Al-Si-Cu layer is deposited at a temperature of at least 400°C.

16. (Cancelled)

17. (Previously Presented) A method of forming a wiring film, the method comprising:

providing a substrate;

depositing an Al_3Ti layer over said substrate;

depositing an Al layer on said Al_3Ti layer;

pattern etching said Al layer; and

after the depositing of the Al layer, annealing the substrate at a temperature of at least 400°C.

18. (Previously Presented) A method as recited in claim 17, wherein said Al layer is deposited at a temperature of at least 400°C.

19. (Cancelled)

20. (Previously Presented) A method as recited in claim 17, wherein said Al_3Ti layer